Robust strong coupling architecture in circuit quantum electrodynamics

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We report on a robust method to achieve strong coupling between a superconducting flux qubit and a high-quality quarter-wavelength coplanar waveguide resonator. We demonstrate the progression from the strong to ultrastrong coupling regime by varying the length of a shared inductive coupling element, ultimately achieving a qubit-resonator coupling strength of 655 MHz, 10% of the resonator frequency. We derive an analytical expression for the coupling strength in terms of circuit parameters and also discuss the maximum achievable coupling within this framework. We experimentally characterize flux qubits coupled to superconducting resonators using one and two-tone spectroscopy methods, demonstrating excellent agreement with the proposed theoretical model.

I. INTRODUCTION

Research over the past few decades has seen significant progress in the field of superconducting quantum circuit (SCQ) making such systems the dominant platform for the realization of novel quantum devices. The framework, incorporating superconducting qubits and cavity resonators, is known by the name circuit quantum electrodynamics (c-QED): the superconducting circuit variant of ‘cavity QED’. Superconducting qubits as two-level systems, also known as ‘artificial atoms’, are the most researched and robust candidates for various applications in the field of c-QED. The advancement in realizing controllable interaction between these artificial atoms and cavities has developed enormously in recent years. Employing a multitude of quantum device architectures, the realization of various qubit-cavity coupling regimes has been explored. The atom-cavity strong coupling regime and ultrastrong coupling regime, where an artificial atom and the cavity exchange a photon many times before the coherence vanishes, has emerged and has been studied extensively.

In this work, we experimentally demonstrate a simple, systematic and robust architecture to achieve strong qubit-resonator coupling. To realize this, we exploit the geometric inductance and nonlinear kinetic inductance of the coupling element by increasing its length and/or decreasing the cross sectional area. The concept of a shared local inductance as a coupling element has been previously explored both theoretically and experimentally. A related approach takes advantage of a large non-linear inductance by embedding a fourth Josephson junction, also known as a ‘coupling junction’. However, the Josephson energy $E_J$, a crucial parameter in flux qubits, is exponentially sensitive to the tunnel barrier thickness, determined mainly by the junction dimensions and oxidation parameters. From fabrication point of view, adding an extra junction adds complexities in the functionality of a flux qubit by influencing the qubit energy levels. Furthermore, optimizing and controlling the coupling junction parameters can be a cumbersome process and challenging in terms of reproducibility and yield. Nevertheless, the architecture of a coupling junction at the constricted central line of a coplanar waveguide (CPW) is a practical choice to achieve ultra strong coupling, while isolating the qubit from magnetic flux noise. References [15–19].

In this paper, we demonstrate the linear dependence of qubit-resonator coupling $g$ while increasing the length dependent inductance of a shared coupling element. Using this robust coupling architecture we show how ultrastrong coupling can be achieved without the use of a coupling junction. Our framework is useful for quantum thermodynamic experiments since the heat current is proportional to the square of the coupling between a qubit and the resonator employed for spectral filtering.

II. DEVICE AND MEASUREMENTS

We report on the fabrication and measurement of seven qubit-resonator systems with varying coupling strengths. As shown in Fig. 1(a), the measured device houses seven λ/4 resonators of varying frequency, capacitively coupled to a common feedline, as shown in Fig. 1(b). The end of each resonator is shunted to a common ground, facilitating inductive coupling to a flux qubit by sharing an inductive element between qubit and the resonator, here labelled a ‘shared edge’, as shown in Fig. 1(d). Depending upon the geometry of this shared edge, the strength of the coupling between qubit and the resonator can vary. Ultra strong coupling is achieved by fabricating the long meandering shared edge structure as shown in Fig. 1(d). Our frequency multiplexing scheme allows us to study multiple flux qubits simultaneously, providing a common platform for comparison. The studied devices are embedded on a 675 µm thick, highly resistive Si wafer. Ground
planes and resonators are formed by etching a 200 nm thick DC sputtered superconducting niobium. Using the Dolan bridge technique, two 30 nm thick layers of aluminium metal are evaporated at design-specific tilt angles interrupted by an in-situ oxidation to form the oxide barrier. The fabrication details are broadly reported in Appendix A. The reliability of fabrication was verified by measuring room temperature resistance of test junctions present in the same fabrication batch. The room temperature resistance of the identical three junction test SQUID Fig. 1(c) is $R \approx 5$ kΩ. The sample is diced using a saw with a thin diamond-embedded resin blade. The device is wire-bonded to a printed circuit board and mounted to the mixing chamber of a commercial dilution refrigerator with a base temperature of 10 mK.

To identify the superconducting resonators, the transmission $S_{21}$ is measured in a broad frequency range by applying a microwave signal from a vector network analyzer (VNA) located at room temperature. Black-body radiation is suppressed using a series of impedance matched attenuators distributed at various temperature stages within the cryostat. The output signal passes through two isolators positioned at the cryostat base temperature, and further amplified by a 42 dB low noise HEMT amplifier mounted at the 4 K stage. Outside the cryostat, the signal is further amplified by 52 dB using two additional room temperature amplifiers. The employed measurement scheme is displayed in Fig. 2(a).

Figure 2(b) shows the measured transmission $S_{21}$ from 5.0 GHz to 7.5 GHz showing the presence of seven peaks, corresponding to seven superconducting resonators of varying frequency. Furthermore, Fig. 2(c) presents a fitted $S_{21}$ transmission corresponding to the qubit with highest measured coupling. The $S_{21}$ scattering parameter expression used to fit the notch-type profile of fabricated superconducting resonators reads:

$$S_{21}^{notch} = a e^{i\alpha} e^{-2\pi i f \tau} \left[ 1 - \frac{(Q_l/Q_c)|e^{i\phi}|}{1 + 2i(Q_l/(f/f_r - 1))} \right].$$

In this expression, $a$ corresponds to the overall signal amplitude, phase shift due to various circuit components is given by $\alpha$ and electronic delays by $|\tau|$. In the ideal resonator part $f$, $f_r$, $Q_l$ and $|Q_c|$ denote the probe frequency, bare resonator frequency, loaded quality factor and the coupling (or external) quality factor in absolute terms, respectively. In Eq. 1 $e^{i\phi}$ signifies the on-chip impedance mismatch, caused by the standing waves and signal asymmetries from different ports. In a resonator $f_r$ and $Q$ are two important characteristics, $f_r$ is length dependent and $|Q_c|$ is determined by the coupling architecture of the resonator to a transmission line. By fitting the $S_{21}$ we determine the internal quality factor $Q_l \approx 5200$, loaded quality factor $Q_l \approx 2800$ and coupling quality factor $Q_c \approx 6000$ of our superconducting resonator. In a resonator $Q_l$ and $|Q_c|$ are the two prominent energy relaxations paths. The total quality factor $Q_l$ of a resonator is given by:

$$Q_l^{-1} = Q_i^{-1} + \text{Re}\{Q_c^{-1}\}.$$
The depth of the notch type transmission profile is defined by the ratio of \( Q_l \) and \( Q_c \), maximizing at the resonator frequency where \( Q_l \approx Q_c \). The photon decay rate \( \kappa/2\pi(=\omega/\Omega_l) \), calculated based on the value of \( Q_l \) from fitting Fig. 2 (c) is 0.37 MHz, corresponding to the photon lifetime \( T_\phi = 1/\kappa \) of 427 ns. For fast spectroscopy measurements to probe the states of a qubit, resonators with moderate quality factor (strongly coupled) are an ideal choice. We then measure the dispersive shift dependence of the diagnostic resonators, as a function of applied flux bias. This is done by measuring the \( S_{21} \) transmission through the common feed line while sweeping the magnet coil current. Due to the coupling between the individual resonators and qubits, the shift from bare resonator frequency is detected while varying the magnet coil current determining the Josephson energy. Furthermore, to locate the individual qubit transitions we perform two-tone spectroscopy. Here, a weak microwave ‘probe tone’ (tone 1), supplied using a VNA, is continuously applied via the readout resonator at a specific magnet coil bias voltage. Once the flux specific probe frequency is located, a ‘pump tone’ (tone two) is applied using a separate microwave signal generator to excite the qubit energy levels. To estimate the coupling strengths, the measured dispersive shift and explored qubit states are fitted using our theoretical model.

III. THEORETICAL MODEL

Here we consider a conventional flux qubit which is composed of a superconducting ring interrupted by three Josephson junctions as shown in Fig. 3. The junctions numbered 1 and 2 are nominally identical with equal critical currents \( I_{C1} = I_{C2} = I_C \) and the critical current of the third junction is \( I_{C3} = \alpha I_C \), where the factor \( \alpha \) (ratio between the area of junction 3 and 1) \( < 1 \). There are two superconducting islands in this setup, the first island \( (G_1) \) is limited by junctions 1 and 2 and the capacitor \( C_{g1} \) with total capacitance of the island \( C_{G1} = C_1 + C_2 + C_{g1} \). The second island \( (G_2) \) is sandwiched by junctions 2 and 3 and the capacitor \( C_{g2} \), with a total capacitance \( C_{G2} = C_2 + C_3 + C_{g2} \). The element between the junction 1 and 3 is shared by both the qubit and the resonator and the inductance of this element is responsible for the qubit-resonator coupling. The phase drop across the shared edge (due to inductance) is \( \varphi = \varphi_1 + \varphi_2 + \varphi_3 - 2\pi \varphi_{ext} \), where \( \varphi_i \) is the phase drop across the \( i \)th junction and \( \varphi_{ext} = 2\pi \Phi_{ext}/\Phi_0 \), while the external magnetic flux is \( \Phi_{ext} \) and \( \Phi_0 = h/2e \) is the magnetic flux quantum. The total Hamiltonian of the system is given as \( H = H_{res} + H_{loop} + H_{int} \), where that of the resonator in terms of the ladder operators \( (a_n, a_n^\dagger) \)and frequency of the \( n \)th mode \( \omega_n \) is \( H_{res} = \sum_{n=0}^{\infty} h\omega_n (a_n^\dagger a_n + \frac{1}{2}) \).

The Hamiltonian of the loop consisting of the qubit and the shared edge is

\[
H_{loop} = \sum_{r,s=1}^{3} 4(E_C)_{rs} n_r n_s + \sum_{j=1}^{3} \hbar I_{Cj} (1 - \cos \varphi_j) + \frac{\hbar^2 \varphi^2}{8e^2 L},
\]

where \( L \) is the inductance of the shared edge. Here \( n_r = -i\partial/\partial \varphi_r \), \( (E_C)_{rs} = e^2(C^{-1})_{rs}/2 \) and the capacitance matrix is

\[
C = \begin{bmatrix} C_1 & 0 & 0 \\ 0 & C_{g1} + C_2 & C_{g1} \\ 0 & C_{g1} & C_{g1} + C_{g2} + C_3 \end{bmatrix}.
\]

The qubit-resonator interaction Hamiltonian is

\[
H_{int} = -\sum_{n=0}^{\infty} \hbar \sqrt{\frac{I_{q0} \hbar^2 \omega_n}{4\pi^2 Z_0}} \varphi(a_n^\dagger a_n) + \sum_{n=0}^{\infty} \frac{R_q}{4\pi^2 Z_0} \hbar \omega_0 \varphi^2,
\]

where \( R_q = h/e^2 \) is the resistance quantum and \( \omega_0 \) is the fundamental frequency of the resonator. Equation 6 is a general case where the summation shows that the phase \( \varphi \) couples to all modes of the resonator. When the bare qubit frequency \( \omega_q \) is close to \( \omega_0 \), for low cryostat temperatures and low power \( S_{21} \) measurements, we can ignore the contributions from higher modes of the resonators and take \( n = 0 \). In our model, the qubit is inductively coupled to the resonator via the shared element and the inductance of the shared edge has two contributions, \( L = L_{geo} + L_{kin} \), where \( L_{geo} \) is the geometric inductance and \( L_{kin} = hR_q/\pi \Delta \) is the kinetic inductance of the aluminum wire, whose resistance

FIG. 3. Circuit diagram of a three junction flux qubit coupled to a resonator. The resonator is capacitively coupled to a transmission line with which a \( S_{12} \) measurement is carried out. There are seven similar qubit-resonator systems coupled to a single transmission line (1-2) as shown in Fig. 1(a).
in normal state is $R_n$ and superconducting gap of aluminum wire $\Delta = 200 \, \mu eV$. The resistivity of the shared edge is estimated in our case to be $5.3 \times 10^{-8} \, \Omega m$, measured at room temperature across an evaporated Al strip of area $\approx 4900 \, \mu m^2$, embedded in the reported device. We explicitly derive (see Appendix B) the coupling in terms of circuit parameters as

$$g \approx \frac{\beta}{L_{l}} \frac{L_{l}^{-1}}{L_{l}^{-1} + C_{eff}^{-1}} \sqrt{\frac{1 - \alpha}{L_{r}}}.$$ \hspace{1cm} (6)

where $L_{l} = L_{1} = L_{2} = \hbar / 2 eI_{C1}$ and $L_{r} = \pi Z_{Q} / 4 \omega$ is the total inductance of the resonator and the effective capacitance of the qubit is given by

$$C_{eff} = \left[ (C_{G1} - 2C_{2})^2 + 4(C_{G2} - C_{2})^2 + 4 \alpha (C_{G1} - 2C_{2}) \right]^{1/2}. \hspace{1cm} (7)$$

Equation (6) is derived for a linearized model, where we replace Josephson junctions with inductors and we get $\beta = 1/2$. This approximation may not be valid close to the flux value $\Phi / \Phi_0 = 0.5$. By fitting with the experimental data, we get $\beta = 1/4$ as shown in Fig. 3. Equation (6) is useful for efficient circuit design as the coupling is expressed in terms of circuit parameters.

IV. RESULTS AND DISCUSSION

It is evident from Eq. (6) that we can increase the coupling by increasing the inductance which in turn can be achieved by increasing the length, or decreasing the thickness of the shared element. The width of the shared edge $w \approx 0.44 \, \mu m$ for the qubits numbered 1, 2, 4, 5, and 6 and length of the shared edge of each of these qubits are different and varies from $l = 10 \, \mu m$ to $l = 120 \, \mu m$, while $w \approx 0.35 \, \mu m$ for the qubits 3 and 7, as shown in Fig. 1(a) and in Table I. We have two sets of qubits with equal length and different widths: the length $l = 30 \, \mu m$ for the qubits 2 and 3, and $l = 120 \, \mu m$ for qubits 6 and 7. In this way inductance of the shared edge varies for all qubits. The thickness of shared edge is approximately 60 nm for all the qubits.

We perform both one-tone and two-tone spectroscopy to characterize the resonators and qubits. By fitting the one-tone spectra, we get the coupling between the qubit and the resonator, and the two-tone spectra provides the qubit transition frequencies. To find the coupling $g$ between qubit and the resonator, in the experiment, we fit the experimental data in the following way. First we find $\omega_q$ by diagonalizing the qubit Hamiltonian in Eq. (3) setting $L = 0$. We use two-dimensional plane waves $\exp(- i n_1 \varphi_1 - i n_3 \varphi_3) / (2 \pi)$ to numerically diagonalize the Hamiltonian (Eq. (4)) to find $\omega_q$. The dressed frequencies of qubit and resonator are given

$$\omega_{q/r} = \frac{1}{\sqrt{2}} \sqrt{\omega_q^2 + \omega_r^2} \pm \sqrt{16 g^2 \omega_q \omega_r + (\omega_q^2 - \omega_r^2)^2}. \hspace{1cm} (8)$$

Using Eq. (8), we fit the data obtained from one-tone and two-tone spectroscopy simultaneously. As an example, spectroscopy of the two qubits, 3 and 7, with shared edge lengths 30 $\mu m$ and 120 $\mu m$ are shown in Fig. 4. The fitted one-tone and two-tone spectra of qubits numbered 1, 2, 4, 5 and 6 are shown in Appendix A. Furthermore, we compare the coupling obtained from the experiments with the estimated coupling from Eq. (6). For qubits numbered 1, 2, 3, 4, 5, and 7, the error in the coupling estimation is typically $\pm 5 \%$, while the error for qubit 6 is $-12 \%, +8 \%$. For each qubit, the error is estimated by varying the coupling term ($g$) within a reasonable
TABLE I. Parameters of the seven qubit-resonator systems shown in Fig. 1(a).

<table>
<thead>
<tr>
<th>No.</th>
<th>l (µm)</th>
<th>w (µm)</th>
<th>ω_r/2π (MHz)</th>
<th>L (nH)</th>
<th>(g/ω_r)100 (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>10</td>
<td>0.44</td>
<td>5.629</td>
<td>0.031</td>
<td>1.40</td>
</tr>
<tr>
<td>2</td>
<td>30</td>
<td>0.44</td>
<td>5.291</td>
<td>0.095</td>
<td>2.74</td>
</tr>
<tr>
<td>3</td>
<td>30</td>
<td>0.35</td>
<td>6.170</td>
<td>0.130</td>
<td>2.91</td>
</tr>
<tr>
<td>4</td>
<td>60</td>
<td>0.44</td>
<td>5.798</td>
<td>0.191</td>
<td>4.19</td>
</tr>
<tr>
<td>5</td>
<td>90</td>
<td>0.44</td>
<td>7.277</td>
<td>0.285</td>
<td>6.39</td>
</tr>
<tr>
<td>6</td>
<td>120</td>
<td>0.44</td>
<td>6.330</td>
<td>0.365</td>
<td>9.32</td>
</tr>
<tr>
<td>7</td>
<td>120</td>
<td>0.35</td>
<td>6.685</td>
<td>0.587</td>
<td>9.80</td>
</tr>
</tbody>
</table>

As illustrated in Fig. 5, the coupling increases linearly with the total inductance of the shared edge. It can be seen from Eq. (6) that by increasing the critical current of the junction (thereby decreasing \( L_J \)) coupling can be increased. It also shows that for \( L \gg \min\{L_r, L_J\} \), the coupling saturates to its maximum value. For \( \alpha = 1/2 \), \( g/\omega_r = L_r/(4[L_r + L_J])\sqrt{C_r/[C_{G1} + 4C_{G2} - 4C_2]} \), with parameters considered in this manuscript, we could achieve a maximum coupling of 25% of resonator frequency.

**Conclusion:** In conclusion, we demonstrate experimentally a simple and robust approach towards achieving high coupling strength between a qubit and resonator by exploiting the length dependent inductance of a galvanic coupling element. We introduce a theoretical model which supports the experimental results, deriving an expression for \( g \) in terms of circuit parameters which is useful for highly efficient design of quantum circuits. Our model with strong coupling between flux type qubits and resonators can play a major role, e.g. in heat transport devices.

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**Appendix A: Fabrication and measurements**

The devices are fabricated on a 675 µm thick, highly resistive Si wafer. A 30 nm thick Al₂O₃ is deposited using atomic layer deposition (ALD), followed by DC magnetron sputtering of a 200 nm superconducting niobium (Nb) layer. For patterning the common feedline, ground plane and resonators, a 300 nm thick positive electron beam resist layer is spin-coated onto the substrate. Nb patterns are exposed by Electron Beam Lithography. After development the sample is post-baked for 5 minutes at 150 °C, followed by reactive ion etching of the exposed parts using CF₄ + O₂ chemistry. Post-baking is done to improve resist adhesion. To create the aluminium layers and Josephson junctions we use the standard Dolan Bridge technique using a bilayer PMMA/MMA resist. After exposure, the top resist layer is developed in Methyl-Isobutyl-Ketone (MIBK):Isopropanol alcohol (IPA) developer solution, and the bottom layer is developed in Methyl-glycol:Methanol solution. Deposition is performed using an e-beam evaporator. In-situ argon plasma milling is used to etch any native oxide formed on the sample surface. A 30 nm thick layer of aluminium metal is evaporated at +18° followed by oxidation to form the barrier oxide. Subsequently, a second 30 nm thick aluminium layer is evaporated at −18°. The evaporated metal from the unexposed part is then lifted-off using acetone. The sample is finally diced and prepared for spectroscopy measurements.
FIG. 6. In each row the figures from left to right represent one tone spectra, two-tone spectra and electron micrograph of qubits reported in Table I.

Appendix B: Theory

Derivation of Eq. (6) in the main text:

We consider the system depicted in Fig. 4 of the main text. To derive an approximate expression for the coupling strength $g$, we linearize the dynamics of the Josephson junctions and approximately replace them by induc-
The classical Lagrangian of the qubit in this approximation takes the form

\[ L_{\text{harm}} = \frac{C_2}{2} \left( \frac{\hbar \phi_2}{2e} \right)^2 + \frac{C_3 + C_{g2}}{2} \left( \frac{\hbar \phi_3}{2e} \right)^2 + \frac{C_1 + C_{g1}}{2} \left( \frac{\hbar \phi_1}{2e} + \frac{\hbar \phi_3}{2e} \right)^2 + \frac{C_1 + C_{g1}}{2} \left( \frac{\hbar \phi_1}{2e} \right)^2 \]

The classical Lagrangian of the qubit in this approximation takes the form

\[ L_{\text{harm}} = \frac{C_2}{2} \left( \frac{\hbar \phi_2}{2e} \right)^2 + \frac{C_3 + C_{g2}}{2} \left( \frac{\hbar \phi_3}{2e} \right)^2 + \frac{C_1 + C_{g1}}{2} \left( \frac{\hbar \phi_1}{2e} \right)^2 \]

Solving the corresponding classical equations of motion for the phases \( \phi_j \), we find the two eigen-frequencies of the qubit,

\[ \omega^2_{q_1, q_2} = \frac{C_{g1}}{L_2} + \frac{C_{g2}}{L_2} + \frac{C_{g2} - 2C_2}{L_2} \]

for the parameters of our qubits the frequency \( \omega_{q_1} \) turns out to be very high. In contrast, the frequency \( \omega_{q_2} \) is lower and it approaches the resonator frequency \( \omega_r \) at flux values close to \( \Phi_0/2 \).

We now include the interaction with the resonator into the model and leave only its fundamental mode with the frequency \( \omega_r \). Afterward, the Lagrangian of the system takes the form

\[ L = \frac{\hbar}{8e^2} \left\{ C_1 \phi^2 - \frac{\phi^2}{L} + (C_1 + C_{g1} + C_{g2} - 2C_2) \phi_3^2 + 2(C_1 - C_2) \phi_2 \phi_3 - \frac{(\phi - \phi_2 - \phi_3)^2}{L_1} - \frac{\phi_2^2}{L_2} - \frac{\phi_3^2}{L_3} - 2C_1 (\phi_2 + \phi_3) \phi + \frac{4}{\pi Z_0 \omega_r} [\phi_n^2 - \omega_n^2 (\phi - \phi)^2] \right\} \]

Here we defined the phase

\[ \phi = \phi_1 + \phi_2 + \phi_3 - (\phi_1^c + \phi_2^c + \phi_3^c). \]

The Lagrangian \([B6]\) describes four coupled oscillators. We define the vector of phases \( \Phi = (\phi, \phi_3, \phi_2, \phi_n) \) and the matrices

\[ M = \begin{pmatrix} C_1 & -C_1 & -C_1 & 0 \\ -C_1 & C_1 + C_{g2} - 2C_2 & C_{g1} - C_2 & 0 \\ -C_1 & C_{g1} - C_2 & C_{g1} - C_2 & 0 \\ 0 & 0 & 0 & C_2 \end{pmatrix} \]

\[ V = \begin{pmatrix} \frac{1}{L_1} + \frac{1}{L_2} + C_r \omega_n^2 & -\frac{1}{L_1} & -\frac{1}{L_1} & -C_r \omega_n^2 \\ -\frac{1}{L_1} & \frac{1}{L_1} + \frac{1}{L_2} & \frac{1}{L_2} & 0 \\ -\frac{1}{L_2} & \frac{1}{L_2} & \frac{1}{L_2} & 0 \\ -C_r \omega_n^2 & 0 & 0 & C_r \omega_n^2 \end{pmatrix} \]

Here \( C_r = 4/\pi Z_0 \omega_r \) is the effective capacitance of the resonator. The eigen-frequencies of the system are determined by the equation

\[ \det [M \omega^2 - V] = 0, \]

which has four solutions. Two of these solutions correspond to the anti-crossing between the resonator mode \( \omega_r \) and the low frequency qubit mode \( \omega_{q_1}(\Phi) \). This anti-crossing can be approximately described by the model of
two coupled oscillators (see also Eq. (7) in the main text)

\[ \omega' \approx \left( \omega_1^2 + \omega_2^2 + \sqrt{(\omega_1^2 - \omega_2^2)^2 + 16g^2\omega_1\omega_2} \right) / 2. \]

\( B9 \)

In our sample the junctions 1 and 2 have the same inductance \( L_1 = L_1 = L_2 = h/2e^2Lc_1 \), while the junction 3 with the weaker critical current has larger inductance \( L_3 = L_1/\alpha \). In addition to that, the condition \( \omega_r \ll \omega_p \), where \( \omega_p = 1/\sqrt{L_1C_1} \) is the plasma frequency of the junctions 1 and 2, is fulfilled. Under these conditions, the qubit frequency \( \omega_{0q}(\Phi) \) approaches the resonator frequency \( \omega_1 \) at \( \Phi \approx \Phi_0/2 \). At this flux point one can approximately solve Eqs. (B2) for the junction phases and, afterwards, Eq. (B9) for the frequencies. Comparing the result with Eq. (B9), we obtain the approximate expression for the coupling constant \( g \) in the form of Eq. (6) with \( \beta = 1/2 \).

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